Complementary Plastic Silicon Power Transistors

These devices are designed for lower power audio amplifier and low current, high–speed switching applications.

Features

- Low Collector–Emitter Sustaining Voltage
- High Current–Gain Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current – Continuous	Ι _Β	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

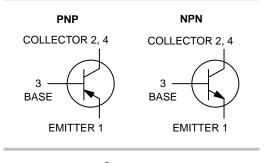
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	8.34	°C/W



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4 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS, 15 WATTS





MARKING DIAGRAM



 $\begin{array}{lll} Y &= Year \\ WW &= Work Week \\ BD78x &= Device Code \\ & x = 7 \ or \ 8 \\ G &= Pb-Free \ Package \end{array}$

ORDERING INFORMATION

Device	Package	Shipping
BD787G	TO–225 (Pb–Free)	500 Units/Box
BD788G	TO-225 (Pb-Free)	500 Units/Box

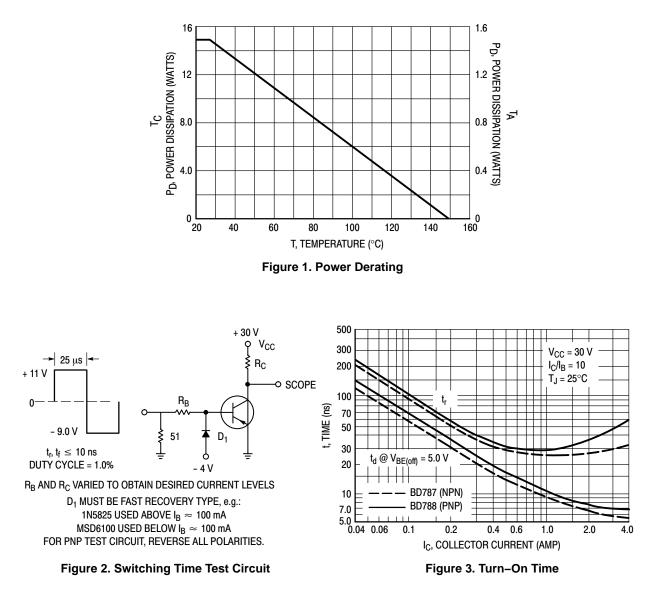
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

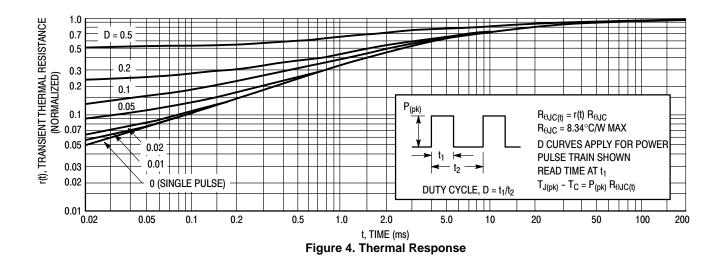
ELECTRICAL CHARACTERISTICS* ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS	· · · · · ·			
Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	-	Vdc
Collector Cutoff Current $(V_{CE} = 20 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	I _{CEO}	-	100	μAdc
Collector Cutoff Current ($V_{CE} = 80 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 40 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc}, T_C = 125^{\circ}C$)	I _{CEX}		1.0 0.1	μAdc mAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	1.0	μAdc
ON CHARACTERISTICS (Note 1)	·			
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 200 \text{ mAdc}, V_{CE} = 3.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) \\ (I_{C} = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) \\ (I_{C} = 4.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) \end{array} $	h _{FE}	40 25 20 5.0	250 _ _ _	_
Collector-Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$) ($I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc}$) ($I_C = 4.0 \text{ Adc}, I_B = 800 \text{ mAdc}$)	V _{CE(sat)}	- - - -	0.4 0.6 0.8 2.5	Vdc
Base–Emitter Saturation Voltage $(I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc})$	V _{BE(sat)}	-	2.0	Vdc
Base-Emitter On Voltage ($I_C = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS			•	·
Current–Gain – Bandwidth Product ($I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 10 \text{ MHz}$)	f _T	50	-	MHz

$(I_{C} = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 10 \text{ MHz})$		50	-	
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_C = 0$)	C _{ob}			pF
BD787G		-	50	
(f = 0.1 MHz) BD788G		-	70	
Small–Signal Current Gain (I _C = 200 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	10	_	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *Indicates JEDEC Registered Data 1. Pulse Test; Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.





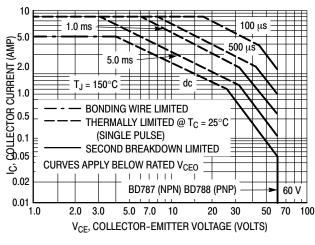
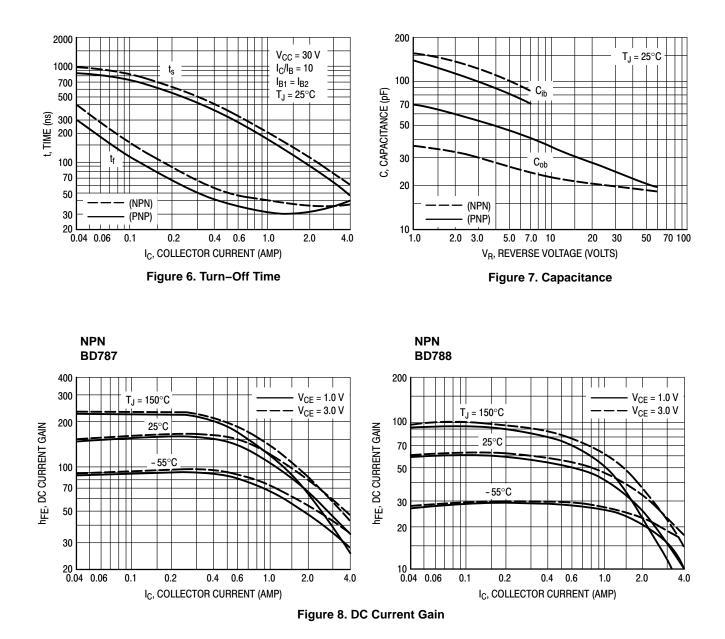


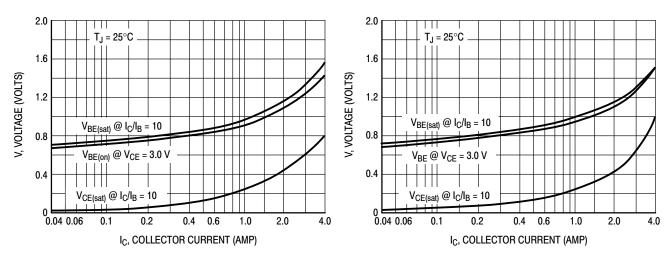
Figure 5. Active Region Safe Operating Area

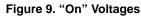
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

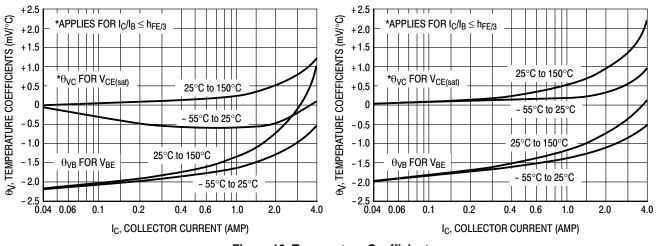
The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}$ C: T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

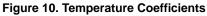


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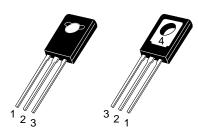








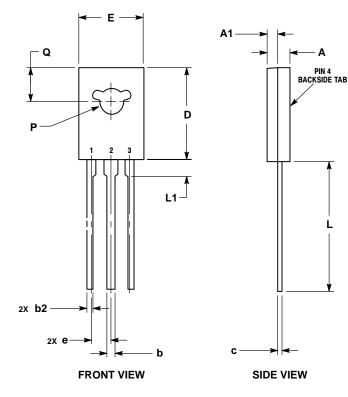
PACKAGE DIMENSIONS



TO-225 CASE 77-09 ISSUE AC

FRONT VIEW

BACK VIEW



NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.

2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
C	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Ρ	2.90	3.30	
Q	3.80	4.20	
STYLE 1: PIN 1. EMITTER 2., 4. COLLECTOR			
BASE			

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